

1. (Amended) A semiconductor laser device, comprising:  
an oxide formed as a protective coating on at least one light emitting end surface  
of a semiconductor laser chip;

B1 an Si film having a film thickness of 40 Å or less formed between the at least one  
light emitting end surface and the oxide protective coating; and

wherein the semiconductor laser device includes an active layer comprised of  
GaAlAs, wherein said active layer is uniform with respect to absorption of an emission  
wavelength throughout its length including at respective end portions thereof.

9. (Amended) A semiconductor laser device, comprising:  
a semiconductor laser chip;  
a protective coating comprising Al<sub>2</sub>O<sub>3</sub> formed on a light emitting end surface of  
the semiconductor laser chip;

B2 an intermediate film comprising silicon having a thickness of 40 Å or less formed  
between the light emitting end surface of the chip and the protective coating comprising  
Al<sub>2</sub>O<sub>3</sub>; and

wherein the semiconductor laser device includes an active layer comprised of  
GaAlAs, wherein said active layer is uniform with respect to absorption of an emission  
wavelength throughout its length including at respective end portions thereof.